NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLY93C** is Designed for Class C, 28V High Band Applications up to 175 MHz.

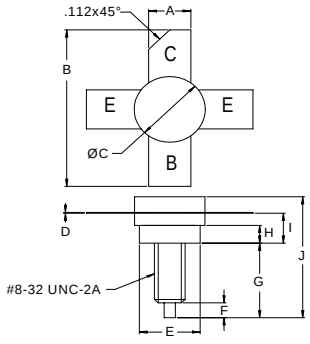
FEATURES:

- P_G = 9.0 dB min. at 25 W/175 MHz
- Common Emitter Configuration
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	70 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA			35			V
BV_{CES}	I_C = 10 mA			65			V
BV_{EBO}	I_E = 10 mA			4.0			V
I_{CES}	V_{CE} = 36 V					4.0	mA
h_{FE}	V_{CE} = 5.0 V	I_C = 1.25 A		10		100	---
C_{ob}	V_{CB} = 28 V		f = 1.0 MHz		45		pF
G_P	V_{CE} = 28 V		f = 175 MHz	9.0			dB
f_T	V_{CB} = 28 V	I_E = 200 mA	f = 100 MHz		625		MHz

Specifications are subject to change without notice.